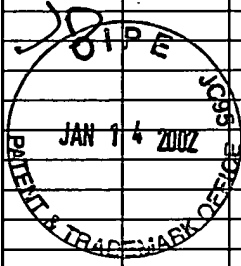


Substitute for form 1449 A & B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>	
				Application Number	09/973,814
				Confirmation Number	7822
				Filing Date	October 11, 2001
				First Named Inventor	Toshiaki KUNIYASU
				Art Unit	2881
Examiner Name	NOT YET ASSIGNED				
Attorney Docket Number	Q66676				
Sheet	1	of	1		

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Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US 6,127,691	A	10/03/00	FUKUNAGA, et al
		US			
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
JD		JP	11-220224		08/10/99		
		JP	11-354880		12/24/99		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
JD		FUKUNAGA, et al "High-Power 0.8 μ m InGaAsP/InGaP/AlGaAs Single Quantum Well :Lasers with Tensile-Strained InGaP Barriers" Jpn. J. Appl. Phys. Vol.38 (1999) pp. L387-L389 Part 2, No. 4A, 1 April 1999	
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Examiner Signature		Date Considered	9/04/03
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.